

## 1200V Silicon Carbide Schottky Diode

#### **DESCRIPTION:**

- High surge current capability
- No reverse recover
- · Positive temperature Coefficient
- · Specified dv/dt ruggedness
- RoHS Compliant

<b>TYPICAL</b>	. APPL	<b>ICAT</b>	IONS	:
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- · Switch mode power supplies
- Solar inverters
- Data Center
- · Power factor correction
- AC/DC converters

$V_{RRM}$	1200V		
I <sub>F</sub>	2A (TC=165°C)		
Qc	12nC		



TO-252 (D-PAK)

### MAXIMUM RATINGS (at T<sub>C</sub> = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V <sub>RRM</sub>	1200	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=165℃	I <sub>F</sub>	11 5 2	А
Non-Repetitive Forward Surge Current	Tc=25°C , $t_P$ =10ms, Half sine pulse Tc=110°C , $t_P$ =10ms, Half sine pulse	I <sub>FSM</sub>	19 14	А
Repetitive Peak Forward Surge Current	Tc=25°C , t <sub>P</sub> =10ms, Half sine pulse	I <sub>FRM</sub>	18	А
i <sup>2</sup> t value	Tc=25 $^{\circ}$ C , t <sub>P</sub> =10ms Tc=110 $^{\circ}$ C , t <sub>P</sub> =10ms	∫ i <sup>2</sup> dt	1.80 0.98	A <sup>2</sup> S
Power dissipation	Tc=25°C Tc=110°C Tc=150°C	P <sub>tot</sub>	108 47 18	W
Operation Junction temperature		Tj	-55~+175	$^{\circ}\!\mathbb{C}$
Storage temperature		T <sub>STG</sub>	-55~+175	$^{\circ}\!\mathbb{C}$

### THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Typical	Unit
Thermal resistance, junction - case		R <sub>th(j-C)</sub>	1.388	°C/W

# ELECTRICAL CHARATERISTICS (at $T_C = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V <sub>DC</sub>	1200			V
Forward Voltage IF = 1A IF = 2A, Tc =25°C IF = 2A, Tc =175°C	V <sub>F</sub>		1.17 1.38 2.0	1.60	V
Reverse Current VR = 1200V, Tc =25°C VR = 1200V, Tc =175°C	I <sub>R</sub>		1 4	50	uA
Total Capacitive Charge VR = 800V	Q <sub>C</sub>		12		nC
Total capacitance VR = 1V, f =1MHz VR = 400V, f =1MHz VR = 800V, f =1MHz	С		125 12 9		pF
Capacitance Stored Energy VR = 800 V	Ec		3.7		uJ

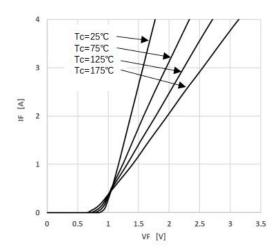


Figure 1. Forward characteristics

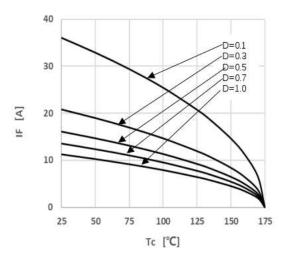


Figure 3. Peak Forward Current Derating

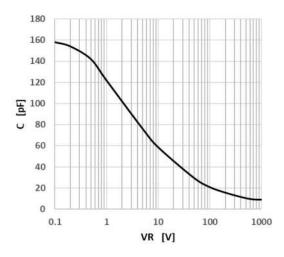


Figure 5. Capacitance vs. Reverse Voltage

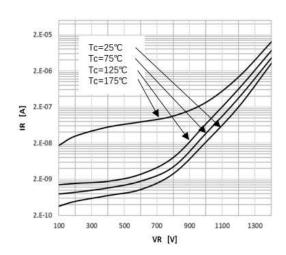


Figure 2. Reverse characteristics

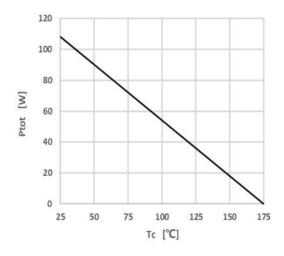


Figure 4. Power Dissipation

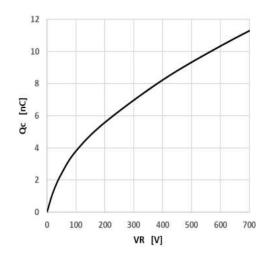
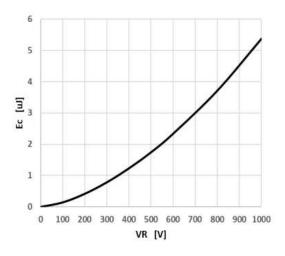


Figure 6. Capacitance Charge vs. Reverse Voltage



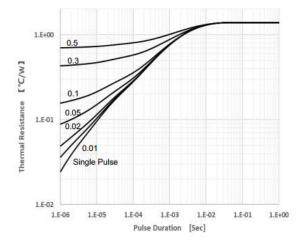


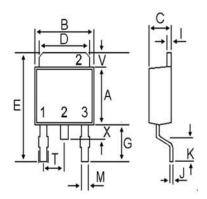
Figure 7. Capacitance Stored Energy

Figure 8. Transient Thermal Impedance

· Circuit diagram



• TO-252-2NC Package outlines : Dimensions in (mm)



DIM	MILLIMETERS			
DIM	MIN	MAX		
Α	5.97	6.22		
В	6.30	6.75		
С	2.18	2.40		
D	4.95	5.46		
E	9.40	10.41		
G	2.75	3.20		
I	0.46	0.89		
J	0.46	0.61		
K	1.40	1.78		
M	0.64	0.89		
Т	2.28	2.30		
V	0.89	1.27		
Х		1.05		



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